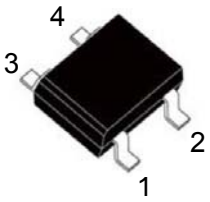
DB201S-DB207S

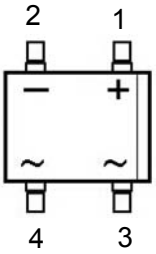
DB-S

RoHS COMPLIANT

Features:

- ☐ Glass passivated chip junction
- ☐ Ideal for surface mounted applications
- ☐ High forward surge current capability
- ☐ High temperature soldering guaranteed: 260℃/10 seconds at terminals
- ☐ Low leakage





Absolute Maximum Ratings (Ta=25℃ unless otherwise noted)

Parameter	Symbol	DB 201S	DB 202S	DB 203S	DB 204S	DB 205S	DB 206S	DB 207S	Unit
Maximum Reverse Peak Repetitive Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Output Current, 0.06"(1.5mm) lead length at Ta=40℃ (Note 1)	$I_{(AV)}$	2.0							A
Peak Forward Surge Current 8.3ms single half sine wave superimposed on rated load (JEDEC Method)	I_{FSM}	60							A
Total Device Dissipation Derate above 25°C	P_D	10.4							W
Maximum Reverse Current @ rated V_R Ta = 25°C Ta = 100°C	I_R	10 1.0							μA mA
Maximum Forward Voltage @ 2.0 A	V_F	1.1							V
Typical Thermal Resistance (NOTE 1)	$R_{\theta JA}$	40							℃/W
Typical Junction Capacitance @V_R = 4.0 V, f = 1.0 MHz	C_j	25							pF
Operating and Storage Temperature Range	Tj, Tstg	-55 to +150							℃

Note :1.Unit mounted on P.C.B. with 0.51"×0.51" (13×13mm) copper pads.

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Typical Characteristics

FIG.1 -- TYPICAL FORWARD CURRENT DERATING CURVE

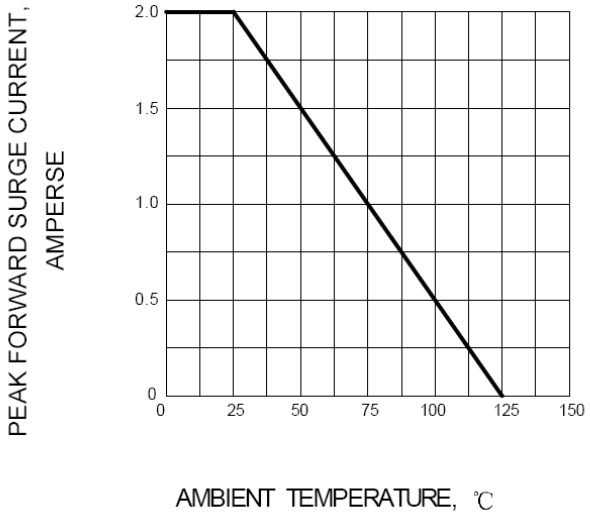


FIG.2 -- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

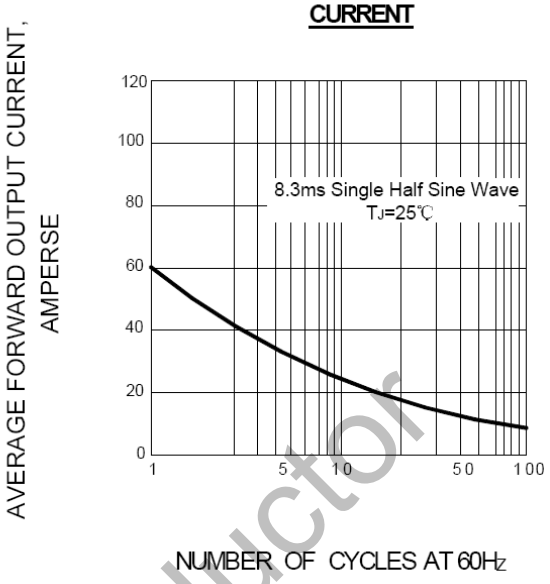


FIG.3 -- TYPICAL FORWARD CHARACTERISTIC

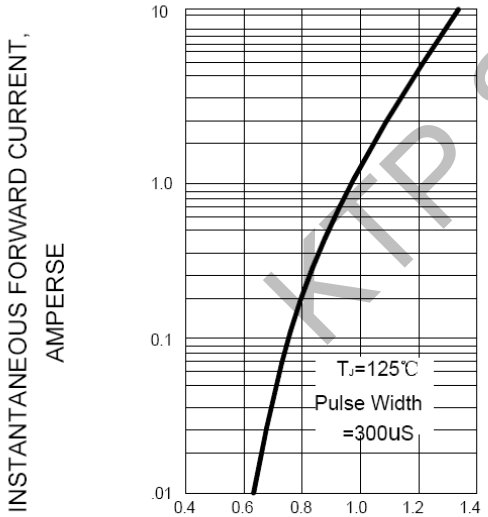
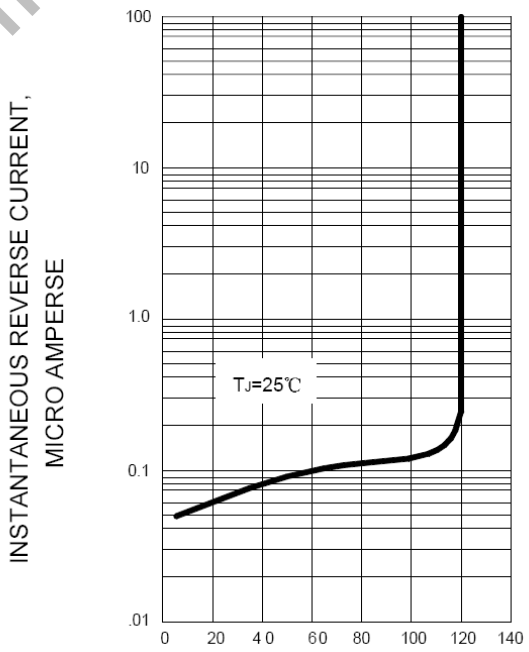


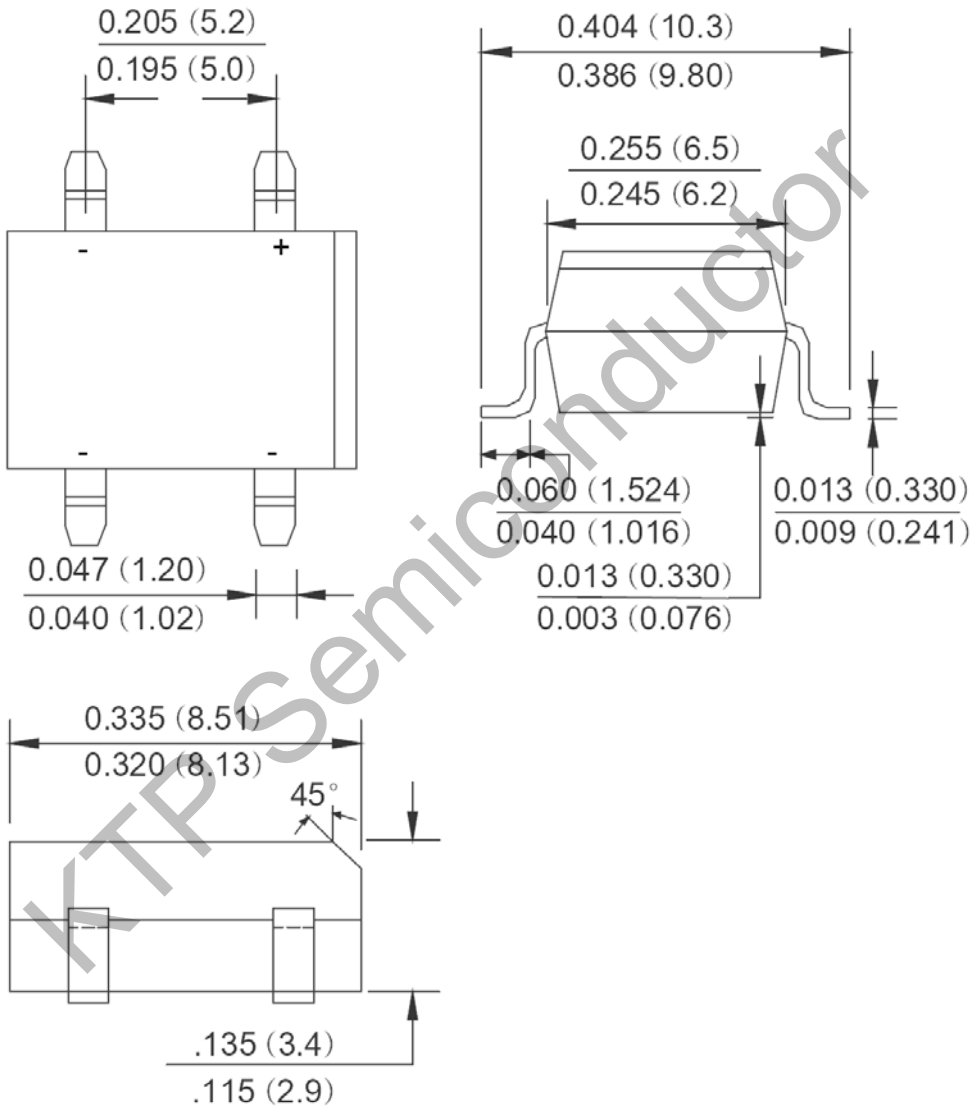
FIG.4 -- TYPICAL REVERSE CHARACTERISTIC



KTP Semiconductor

Package Dimension

DB-S



Dimensions in inches and (millimeters)

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